

LP8556 High-Efficiency LED Backlight Driver for Tablets

Check for Samples: LP8556

FEATURES

- High-Efficiency DC/DC Boost Converter with Integrated 0.19Ω Power MOSFET and Three Switching Frequency Options: 312 / 625 / 1250 kHz
- 2.7V to 36V Boost Switch Input Voltage Range Supports Multi-cell Li-Ion Batteries (2.7V - 20V VDD Input Range)
- 7V to 43V Boost Switch Output Voltage Range Supports as few as 3 WLEDs in Series per Channel and as Many as 12
- Configurable Channel Count (1 to 6)
- Up to 50 mA per Channel
- PWM and / or I²C™ Brightness Control
- Phase-Shift PWM Mode Reduces Audible Noise
- Adaptive Dimming for Higher LED Drive Optical Efficiency

- Programmable Edge-rate Control and Spread Spectrum Scheme Minimize Switching Noise and Improve EMI Performance
- LED Fault (short/open) Detection, UVLO, TSD, OCP and OVP (up to 6 Threshold Options)
- Available in tiny 20-bump, 1.715 mm x 2.376 mm x 0.6 mm, 0.4 mm pitch, DSBGA Package, and 24-pad, 4 mm x 4 mm x 0.8 mm, 0.5 mm Pitch, WQFN Package.

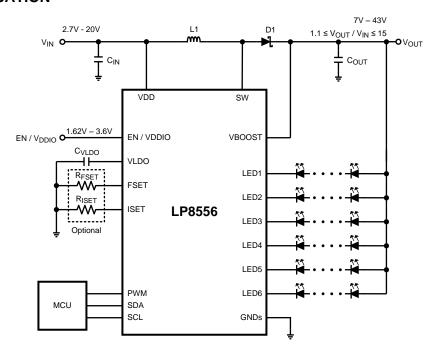
APPLICATIONS

• Tablet LCD Display LED Backlight

DESCRIPTION

LP8556 is a white LED driver featuring an asynchronous boost converter and six high precision current sinks that can be controlled by a PWM signal or an I²C master.

TYPICAL APPLICATION



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DESCRIPTION (CONTINUED)

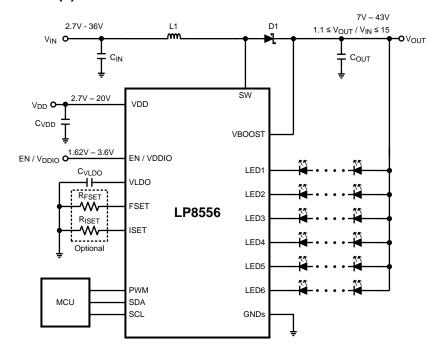
The boost converter uses adaptive output voltage control for setting the optimal LED driver voltages as low as 7V and as high as 43V. This feature minimizes the power consumption by adjusting the output voltage to the lowest sufficient level under all conditions. The converter can operate at three switching frequencies: 312, 625 and 1250 kHz settable with an external resistor or pre-configured via EPROM. Programmable slew rate control and spread spectrum scheme minimize switching noise and improve EMI performance.

LED current sinks can be set with the PWM dimming resolution of up to 15 bits. Proprietary adaptive dimming mode allows higher system power saving. In addition, phase shifted LED PWM dimming allows reduced audible noise and smaller boost output capacitors.

The LP8556 has a full set of safety features that ensure robust operation of the device and external components. The set consists of input under-voltage lockout, thermal shutdown, over-current protection, up to 6 levels of over-voltage protection, LED open and short detection.

The LP8556 operates over the ambient temperature range of -30°C to +85°C. It is available in space-saving 20-bump DSBGA and 24-pad WQFN packages.

TYPICAL APPLICATION (2)





Recommended Inductance for the Boost Power Stage

Assumes 20 mA as the maximum LED current per string and 3.3V as the maximum LED forward voltage.

Number of LED	Number of LEDs per	Boost Input Voltage	L1 Inductance [μH]				
Strings	String	String Range [V]		f _{SW} = 625 kHz	f _{SW} = 312 kHz		
6	6	2.7V - 4.4V	3.3 μΗ - 6.8 μΗ	6.8 μH - 15 μH	10 μΗ - 33 μΗ		
6	6	5.4V - 8.8V	10 μH - 22 μΗ	22 μΗ - 47 μΗ	47 μΗ - 100 μΗ		
^	8	2.7V - 4.4V	4.7 μΗ - 10 μΗ	10 μΗ - 15 μΗ	22 μΗ - 33 μΗ		
6		5.4V - 8.8V	10 μH - 22 μΗ	22 μΗ - 68 μΗ	47 μΗ - 100 μΗ		
4	10	5.4V - 8.8V	6.8 µH - 22 µH	22 μΗ - 47 μΗ	47 μΗ - 100 μΗ		
4	12	5.4V - 8.8V	10 μΗ - 22 μΗ	22 μΗ - 47 μΗ	33 μH - 100 μH		

Recommended Capacitances for the Boost and LDO Power Stages (1)

Switching Frequency [kHz]	C _{IN} [μF]	C _{OUT} [µF]	C _{VLDO} [μF]
1250	2.2	4.7	10
625	2.2	4.7	10
312	4.7	10	10

⁽¹⁾ Capacitance of Multi Layer Ceramic Capacitors (MLCC) can change significantly with the applied DC voltage. Use capacitors with good capacitance vs. DC bias characteristics. In general, MLCC in bigger packages have lower capacitance de-rating than physically smaller capacitors.



Connection Diagrams (DSBGA)

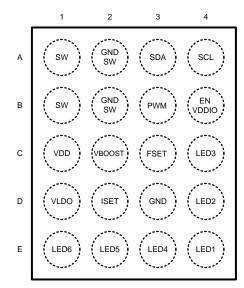


Figure 1. 20-bump DSBGA Package – Top View See Package Number YFQ0020

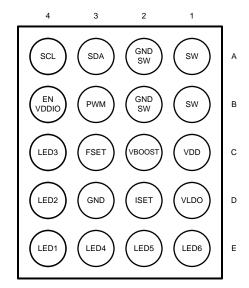


Figure 2. Bottom View

Connection Diagrams (WQFN)

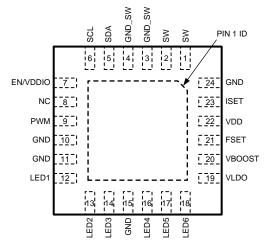


Figure 3. 24-pin WQFN Package - Top View See Package Number RTW0024A

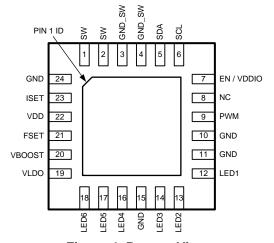


Figure 4. Bottom View



PIN DESCRIPTIONS

uSMD	WQFN	Name	Type ⁽¹⁾	Description
A1, B1	1, 2	SW	A	A connection to the drain terminal of the integrated power MOSFET.
A2, B2	3, 4	GND_SW	G	A connection to the source terminal of the integrated power MOSFET.
A3	5	SDA	I/O	I ² C data input/output pin.
A4	6	SCL	I	I ² C clock input pin.
В3	9	PWM	1	PWM dimming input. Supply a 75 Hz to 25 kHz PWM signal to control dimming. This pin must be connected to GND if unused.
В4	7	EN / VDDIO	Р	Dual purpose pin serving both as a Chip enable and as a power supply reference for PWM, SDA and SCL inputs. Drive this pin with a logic gate capable of sourcing a minimum of 1 mA.
C1	22	VDD	Р	Device power supply pin. Provide 2.7V to 20V supply to this pin. This pin is an input of the internal LDO regulator. The output of the internal LDO is what powers the device.
C2	20	VBOOST	А	Boost converter output pin. The internal Feedback (FB) and Overvoltage Protection (OVP) circuitry monitors the voltage on this pin. Connect the converter output capacitor bank close to this pin.
C3	21	FSET	A	A connection for setting the boost frequency and PWM output dimming frequency by using an external resistor. Connect a resistor, R _{FSET} , between this pin and the ground reference (See Table 5). This pin may be left floating if PWM_FSET_EN=0 AND BOOST_FSET_EN=0 (See Table 9).
C4	14	LED3	Α	LED driver - current sink terminal. If unused, it may be left floating.
D1	19	VLDO	Р	Internal LDO output pin. Connect a capacitor, C _{VLDO} , between this pin and the ground reference.
D2	23	ISET	А	A connection for the LED current set resistor. Connect a resistor, R _{ISET} , between this pin and the ground reference. This pin may be left floating if ISET_EN=0 (See Table 9).
D3	10, 11, 15, 24, DAP	GND	I	Ground pin.
D4	13	LED2	Α	LED driver - current sink terminal. If unused, it may be left floating.
E1	18	LED6	Α	LED driver - current sink terminal. If unused, it may be left floating.
E2	17	LED5	Α	LED driver - current sink terminal. If unused, it may be left floating.
E3	16	LED4	Α	LED driver - current sink terminal. If unused, it may be left floating.
E4	12	LED1	Α	LED driver - current sink terminal. If unused, it may be left floating.
-	8	NC	-	No Connect pin.

(1) A: Analog Pin, G: Ground Pin, P: Power Pin, I: Digital Input Pin, I/O: Digital Input/Output Pin



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.



ABSOLUTE MAXIMUM RATINGS(1)(2)

	Min	Max	Units
V_{DD}	-0.3	24	V
Voltage on Logic Pins (SCL, SDA, PWM)	-0.3	6	V
Voltage on Analog Pins (VLDO, EN / VDDIO)	-0.3	6	V
Voltage on Analog Pins (FSET, ISET)	-0.3	VLDO+0.3	V
V (LED1LED6,SW, VBOOST)	-0.3	50	V
Junction Temperature (T _{J-MAX}) ⁽³⁾		125	°C
Storage Temperature Range	-65	150	°C
Maximum Lead Temperature (Soldering)		260	°C
HBM ⁽⁴⁾	2		kV
CDM ⁽⁵⁾	500		V

- (1) If Military/Aerospace specified devices are required, please contact the Texas Instruments Sales Office/ Distributors for availability and specifications.
- (2) Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability, see the Electrical Characteristics tables.
- (3) In applications where high power dissipation and/or poor package thermal resistance is present, the maximum ambient temperature may have to be de-rated. Maximum ambient temperature (T_{A-MAX}) is dependent on the maximum operating junction temperature ($T_{J-MAX-OP} = 125$ °C), the maximum power dissipation of the device in the application (P_{D-MAX}), and the junction-to ambient thermal resistance of the part/package in the application (θ_{JA}), as given by the following equation: $T_{A-MAX} = T_{J-MAX-OP} (\theta_{JA} \times P_{D-MAX})$.
- (4) Min and Max limits are specified by design, test, or statistical analysis. Typical numbers are not verified, but do represent the most likely norm.
- (5) Field Induced Charge Device Model, applicable std. JESD22-C101-C

OPERATING RATINGS(1)(2)

	Min	Max	Units
VDD Range	2.7	20	V
EN / VDDIO Range	1.62	3.6	V
V (LED1LED6, SW, VBOOST)	0	48	V
Junction Temperature Range (T _J)	-30	125	°C
Ambient Temperature Range (T _A)	-30	85	°C

⁽¹⁾ Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability, see the Electrical Characteristics tables.

THERMAL PROPERTIES(1)

	Min	Max	Units
Junction-to-Ambient Thermal Resistance (θ_{JA}), DSBGA Package	40	73	°C/W
Junction-to-Ambient Thermal Resistance (θ_{JA}), WQFN Package	35	50	°C/W

 Junction-to-ambient thermal resistance is highly application and board-layout dependent. In applications where high maximum power dissipation exists, special care must be paid to thermal dissipation issues in board design.

⁽²⁾ All voltages are with respect to the potential at the GND pins.



ELECTRICAL CHARACTERISTICS(1)(2)

Limits in standard typeface are for $T_A = 25$ °C. Limits in **boldface** type apply over the full operating ambient temperature range (-30 °C $\leq T_A \leq$ +85 °C). Unless otherwise specified: VDD=12V, EN / VDDIO = 1.8V

Symbol	Parameter	Condition	Min	Тур	Max	Units
V_{DDIO}	Supply voltage for digital I/Os		1.62		3.6	V
V_{DD}	Input voltage for the internal LDO		2.7		20	V
	Standby Supply Current	EN / VDDIO=0V, LDO disabled			1.6	μA
I_{DD}		LDO enabled, Boost disabled		0.9	1.5	^
	Normal Mode Supply Current	LDO enabled, Boost enabled, no load		2.2	0.9 1.5 2.2 3.65 +4 +7	mA
f _{OSC}	Internal Oscillator Frequency Accuracy		-4 -7			%
		V _{DD} ≥ 3.1V	2.95	3.05	3.15	
V_{LDO}	LDO Output Voltage	2.7V ≤ V _{DD} < 3.1V		V _{DD} - 0.05		V
T _{TSD}	Thermal Shutdown Threshold	See ⁽³⁾		150		°C
T _{TSD_hyst}	Thermal Shutdown Hysteresis			20		°C

- (1) All voltages are with respect to the potential at the GND pins.
- (2) Min and Max limits are verified by design, test, or statistical analysis. Typical numbers are for information only.
- (3) Verified by design and not tested in production.

BOOST CONVERTER ELECTRICAL CHARACTERISTICS (1)

Symbol	Parameter	(Condition	Min	Тур	Max	Units	
R _{DS_ON}	Switch ON resistance	I _{SW} = 0.5A			0.19		Ω	
V _{BOOST_MIN}	Boost minimum output voltage	VBOOST_RANGE = VBOOST_RANGE =			7 16		V	
		VBOOST_MAX = 10 VBOOST_MAX = 12	00, VBOOST_RANGE = 0 01, VBOOST_RANGE = 0 10, VBOOST_RANGE = 0 11, VBOOST_RANGE = 0	19.0 24.0 28.0 32	21 25 30 34	22 27 32 37	٧	
V _{BOOST_MAX}	Boost maximum output voltage	VBOOST_MAX = 0' VBOOST_MAX = 10' VBOOST_MAX = 10' VBOOST_MAX = 1'	10, VBOOST_RANGE = 1 11, VBOOST_RANGE = 1 20, VBOOST_RANGE = 1 21, VBOOST_RANGE = 1 10, VBOOST_RANGE = 1 11, VBOOST_RANGE = 1	17.9 22.8 27.8 32.7 37.2 41.8	21 25 30 34.5 39 43	23.1 27.2 31.5 36.6 40.8 44.2	V	
	Maximum continuous output	V _{IN} = 3V, V _{OUT} = 18			220		_	
I _{LOAD_MAX}	load current	$V_{IN} = 3V, V_{OUT} = 24V$			160		mA	
		$V_{IN} = 3V, V_{OUT} = 30$	V		120	4.5		
V _{OUT} /V _{IN}	Conversion ratio (2)	f _{SW} = 625 kHz				15		
		f _{SW} = 1250 kHz				12		
f_{SW}	Switching frequency	BOOST_FREQ = 00 BOOST_FREQ = 01 BOOST_FREQ = 10			312 625 1250		kHz	
V _{OVP}	Over-voltage protection voltage	VBOOST_RANGE =	- 1		V _{BOOST} + 1.6V		V	
		UVLO_EN = 1						
V_{UVLO}	V _{IN} under-voltage lockout threshold	UVLO_TH = 0, fallin UVLO_TH = 1, fallin			2.5 5.2		V	
		V _{UVLO} [rising]	UVLO_TH = 0		50		.,	
V_{UVLO_hyst}	V _{UVLO} hysteresis	V _{UVLO} [falling]	UVLO_TH = 1		100		mV	
t _{PULSE}	Switch minimum pulse width	no load	1		50		ns	
t _{STARTUP}	Startup time	See ⁽³⁾			8		ms	

⁽¹⁾ Min and Max limits are specified by design, test, or statistical analysis. Typical numbers are not verified, but do represent the most likely norm.

⁽²⁾ Verified by design and not tested in production.

³⁾ Startup time is measured from the moment boost is activated until the VBOOST crosses 90% of its target value.



BOOST CONVERTER ELECTRICAL CHARACTERISTICS(1) (continued)

Symbol	Parameter	C	Condition	Min	Тур	Max	Units
I _{SW LIM}	SW pin current limit ⁽⁴⁾	IBOOST_LIM_2X = 0	IBOOST_LIM = 00 IBOOST_LIM = 01 IBOOST_LIM = 10 IBOOST_LIM = 11	0.66 0.88 1.12 1.35	0.9 1.2 1.5 1.8	1.16 1.40 1.73 2.07	А
OVV_E.IIVI	,	IBOOST_LIM_2X = 1	IBOOST_LIM = 00 IBOOST_LIM = 01 IBOOST_LIM = 10		1.6 2.1 2.6	1.16 1.40 1.73	А
ΔV _{SW} / t _{off_on}	SW pin slew rate during OFF to ON transition	EN_DRV3 = 0 AND EN_DRV3 = 0 AND EN_DRV3 = 1 AND	EN_DRV2 = 1		3.7 5.3 7.5		V / ns
ΔV_{SW} / t_{on_off}	SW pin slew rate during ON to OFF transition	EN_DRV3 = 0 AND EN_DRV3 = 0 AND EN_DRV3 = 1 AND	EN_DRV2 = 1		1.9 4.4 4.8		V / ns
Δt _{ON} / t _{SW}	Peak to peak switch ON time deviation to SW period ratio (Spread spectrum feature)	SSCLK_EN = 1			1		%

^{1.8}A is the maximum I_{SW_LIM} supported with the DSBGA package. For applications requiring the I_{SW_LIM} to be greater than 1.8A and up to 2.6A, WQFN package should be considered.

LED DRIVER ELECTRICAL CHARACTERISTICS(1)

Symbol	Parameter	Condition	Min	Тур	Max	Units
I _{LED_LEAKAGE}	Leakage current	Outputs LED1LED6, V _{OUT} = 48V		0.1	1	μΑ
I _{LED_MAX}	Maximum Sink Current LED1LED6			50		mA
I _{LED}	LED Current Accuracy ⁽²⁾	Output current set to 23 mA	-3 -4	1	+3 +4	%
I _{MATCH}	Matching	Output current set to 23 mA		0.5		%
		100 Hz < f _{PWM} ≤ 200 Hz	0.02		100	
		200 Hz < f _{PWM} ≤ 500 Hz	0.02		100	
		500 Hz < f _{PWM} ≤ 1 kHz	0.02		100	
		1 kHz < f _{PWM} ≤ 2 kHz	0.04		100	
PWM_{DUTY}	LED PWM output pulse duty cycle ⁽³⁾	2 kHz < f _{PWM} ≤ 5 kHz	0.1		100	%
	oyolo .	5 kHz < f _{PWM} ≤ 10 kHz	0.2		1 +3 +4 .5 .5 .5	
		10 kHz < f _{PWM} ≤ 20 kHz	0.4		100	
		20 kHz < f _{PWM} ≤ 30 kHz	0.6		100	
		30 kHz < f _{PWM} ≤ 39 kHz	0.8		100	
f _{LED}	PWM output frequency	PWM_FREQ = 1111		38.5		kHz
V _{SAT}	Saturation Voltage ⁽⁴⁾	Output current set to 23 mA		200		mV

- (1) Min and Max limits are specified by design, test, or statistical analysis. Typical numbers are not verified, but do represent the most likely
- Output Current Accuracy is the difference between the actual value of the output current and programmed value of this current. Matching is the maximum difference from the average. For the constant current sinks on the part (OUT1 to OUT6), the following are determined: the maximum output current (MAX), the minimum output current (MIN), and the average output current of all outputs (AVG). Two matching numbers are calculated: (MAX-AVG)/AVG and (AVG-MIN/AVG). The largest number of the two (worst case) is considered the matching figure. The typical specification provided is the most likely norm of the matching figure for all parts. Note that some manufacturers have different definitions in use.
- (3) Verified by design and not tested in production.
- Saturation voltage is defined as the voltage when the LED current has dropped 10% from the value measured at 1V.

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PWM INTERFACE CHARACTERISTICS(1)

Symbol	Parameter	Condition	Min	Тур	Max	Units
f _{PWM}	PWM Frequency Range (2)		75		25000	Hz
t _{MIN_ON}	Minimum Pulse ON time			1		
t _{MIN_OFF}	Minimum Pulse OFF time			1		μs
t _{STARTUP}	Turn on delay from standby to backlight on	PWM input active, VDDIO pin transitions from 0V to 1.8V.		10		ms
t _{STBY}	Turn off delay	PWM input low time for turn off		50		ms
PWM _{RES}	PWM Input Resolution	f _{IN} < 9.0 kHz		8		bits

- (1) Min and Max limits are specified by design, test, or statistical analysis. Typical numbers are for information only.
- (2) Verified by design and not tested in production.

LOGIC INTERFACE CHARACTERISTICS(1)

Symbol	Parameter	Condition	Min	Тур	Max	Units
Logic Inp	uts (PWM, SDA, SCL)				•	
V _{IL}	Input Low Level				0.3 X VDDIO	V
V _{IH}	Input High Level		0.7 X VDDIO			V
I _I	Input Current	$(V_{DDIO} = 0V \text{ or } 3.6V) \text{ AND}$ $(V_I = 0V \text{ or } 3.6V)$	-1.0		1.0	μΑ
Logic Ou	tputs (SDA)					
V _{OL}	Output Low Level	I _{OUT} = 3 mA (pull-up current)		0.3	0.4	V
IL	Output Leakage Current	V _{OUT} = 5V	-1.0		1.0	μΑ

⁽¹⁾ Min and Max limits are specified by design, test, or statistical analysis. Typical numbers are for information only.

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I²C SERIAL BUS TIMING PARAMETERS (SDA, SCL)⁽¹⁾

Cumbal	Dovemeter	Lim	it	Units
Symbol	Parameter		Max	Units
f _{SCL}	Clock Frequency		400	kHz
1	Hold Time (repeated) START Condition	0.6		μs
2	Clock Low Time	1.3		μs
3	Clock High Time	600		ns
4	Setup Time for a Repeated START Condition	600		ns
5	Data Hold Time	50		ns
6	Data Setup Time	100		ns
7	Rise Time of SDA and SCL	20+0.1C _b	300	ns
8	Fall Time of SDA and SCL	15+0.1C _b	300	ns
9	Set-up Time for STOP condition	600		ns
10	Bus Free Time between a STOP and a START Condition	1.3		μs
C _b	Capacitive Load Parameter for Each Bus Line Load of 1 pF corresponds to 1 ns.	10	200	ns

(1) Verified by design and not tested in production.

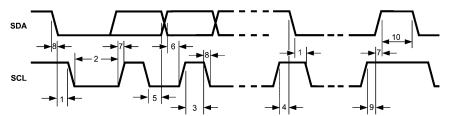
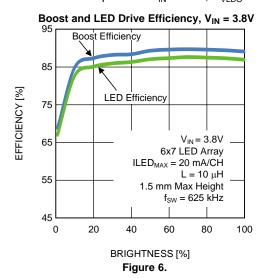


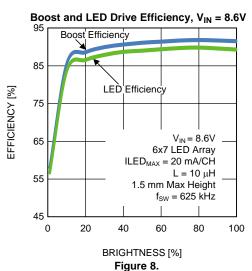
Figure 5. I²C-Compatible Timing

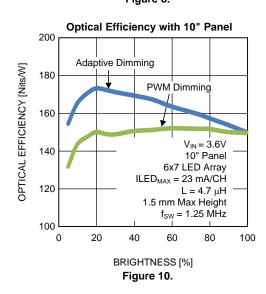


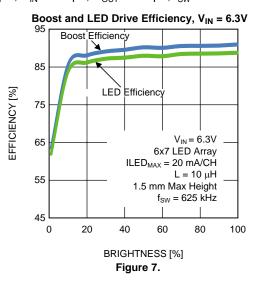
TYPICAL PERFORMANCE CHARACTERISTICS

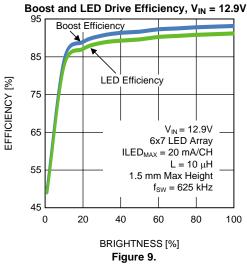
Unless otherwise specified: V_{IN} = 3.8V, C_{VLDO} = 10 μ F, L1 = 4.7 μ H, C_{IN} = 2.2 μ F, C_{OUT} = 4.7 μ F, f_{SW} = 1.25 MHz

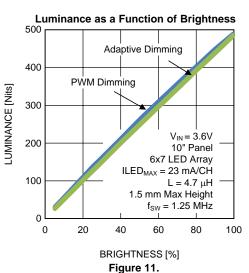








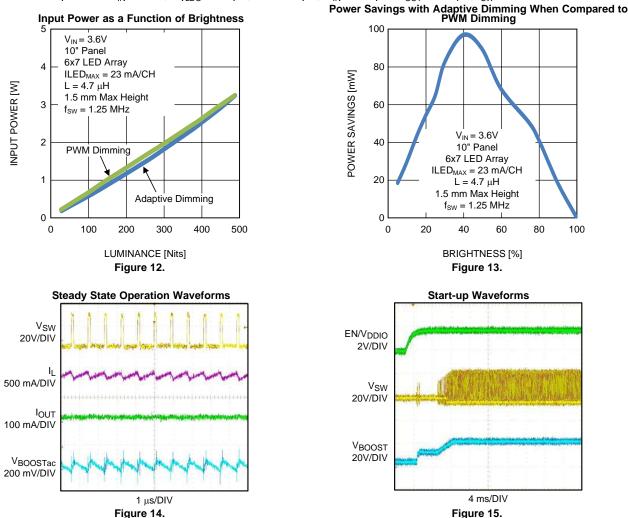






TYPICAL PERFORMANCE CHARACTERISTICS (continued)

Unless otherwise specified: V_{IN} = 3.8V, C_{VLDO} = 10 μ F, L1 = 4.7 μ H, C_{IN} = 2.2 μ F, C_{OUT} = 4.7 μ F, f_{SW} = 1.25 MHz



FUNCTIONAL OVERVIEW

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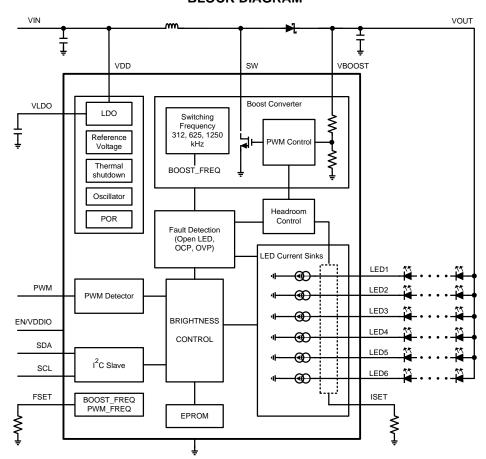
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BLOCK DIAGRAM





Boost Converter Overview

OPERATION

The LP8556 boost DC/DC converter generates a 7V to approximately 43V boost output voltage from a 2.7V to 36V boost input voltage. The boost output voltage minimum, maximum value and range can be set digitally by pre-configuring EPROM memory (VBOOST RANGE, VBOOST and VBOOST MAX fields).

The converter is a magnetic switching PWM mode DC/DC boost converter with a current limit. It uses CPM (current programmed mode) control, where the inductor current is measured and controlled with the feedback. During startup, the soft-start function reduces the peak inductor current. LP8556 has an internal 20 MHz oscillator which is used for clocking the boost. The following figure shows the boost block diagram.

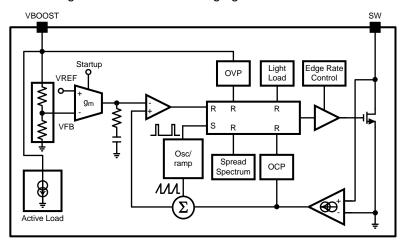


Figure 16. LP8556 Boost Converter Block Diagram

SETTING BOOST SWITCHING FREQUENCY

The LP8556 boost converter switching frequency can be set either by an external resistor (BOOST_FSET_EN = 1 selection), R_{FSET} , or by pre-configuring EPROM memory with the choice of boost frequency (BOOST_FREQ field). Table 1 summarizes setting of the switching frequency. Note that the R_{FSET} is shared for setting the PWM dimming frequency in addition to setting the boost switching frequency. Setting the boost switching frequency and PWM dimming frequency using an external resistor is separately shown in Table 5.

Table 1. Configuring Boost Switching Frequency via EPROM

R _{FSET} [Ω]	BOOST_FSET_EN	BOOST_FREQ[1:0]	f _{SW} [kHz]
don't care	0	00	312
don't care	0	01	625
don't care	0	10	1250
don't care	0	11	undefined
(1)	1	don't care	(1)

(1) See Table 5



OUTPUT VOLTAGE CONTROL

LP8556 supports two modes of controlling the Boost output voltage, Adaptive Boost Voltage Control and Manual Boost Output Control. Each of the two modes are detailed below.

Adaptive Control:

LP8556 supports a mode of output voltage control called Adaptive Boost Control mode. In this mode, the voltage at the LED pins is periodically monitored by the control loop and adaptively adjusted to the optimum value based on the comparator thresholds set using LED DRIVER_HEADROOM, LED_COMP_HYST, BOOST_STEP_UP, BOOST_STEP_DOWN fields in the EPROM. Settings under LED DRIVER_HEADROOM along with LED_COMP_HYST fields determine optimum boost voltage for a given condition. Boost voltage will be raised if the voltage measured at any of the LED strings falls below the threshold setting determined with LED DRIVER_HEADROOM field. Likewise, boost voltage will be lowered if the voltage measured at any of the LED strings is above the combined setting determined under LED DRIVER_HEADROOM and LED_COMP_HYST fields. LED_COMP_HYST field serves to fine tune the headroom voltage for a given peak LED current. The boost voltage up/down step size can be controlled with the BOOST_STEP_UP and BOOST_STEP_DN fields.

The initial boost voltage is configured with the VBOOST field. This field also sets the minimum boost voltage. The VBOOST_MAX field sets the maximum boost voltage. When an LED pin is open, the monitored voltage will never have enough headroom and the adaptive mode control loop will keep raising the boost voltage. The VBOOST_MAX field allows the boost voltage to be limited to stay under the voltage rating of the external components.

NOTE

Only LED strings that are enabled are monitored and PS_MODE field determines which LED strings are enabled.

This Adaptive mode is selected using ADAPTIVE bit set to 1 (CFGA EPROM Register) and is the recommended mode of boost control.

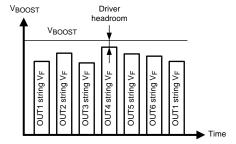


Figure 17. Boost Adaptive Control Principle

Manual Control:

User can control the boost output voltage with the VBOOST EPROM field when adaptive mode is not used. The following expression shows the relationship between the boost output voltage and the VBOOST field:

$$V_{BOOST} = V_{BOOST_MIN} + 0.42*VBOOST[dec]$$
 (1)

The expression is only valid when the calculated values are between the minimum boost output voltage and the maximum boost output voltage. The minimum boost output voltage is set with the VBOOST_RANGE field. The maximum boost output voltage is set with the VBOOST_MAX EPROM field.

Product Folder Links: LP8556

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EMI REDUCTION

The LP8556 features two EMI reduction schemes.

The first scheme, Programmable Slew Rate Control, uses a combination of three drivers for boost switch. Enabling all three drivers allows boost switch on/off transition times to be the shortest. On the other hand, enabling just one driver allows boost switch on/off transition times to be the longest. The longer the transition times, the lower the switching noise on the SW terminal. It should also be noted that the shortest transition times bring the best efficiency as the switching losses are the lowest.

EN_DRV2 and EN_DRV3 bits in the EPROM determine the boost switch driver configuration. Refer to the SW pin slew rate parameter listed under BOOST CONVERTER ELECTRICAL CHARACTERISTICS for the slew rate options.

The second EMI reduction scheme is the spread spectrum scheme which deliberately spreads the frequency content of the boost switching waveform, which inherently has a narrow bandwidth, makes the switching waveform's bandwidth wider and ultimately reduces its EMI spectral density.

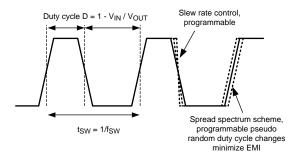


Figure 18. Principles of EMI Reduction Scheme

Brightness Control

LP8556 enables various methods of brightness control. The brightness can be controlled using an external PWM signal or the Brightness register accessible by users via an I^2C interface or both. How these two input sources are selected and combined is set by the BRT_MODE EPROM bits and described in the following sections, Figure 19, and Table 2. The LP8556 can also be preconfigured via EPROM memory to allow direct and unaltered brightness control by an external PWM signal. This mode of operation is obtained by setting PWM_DIRECT EPROM bit to '1' (CFG5[7] = 1).

BRT MODE = 00

With BRT_MODE = 00, the LED output is controlled by the PWM input duty cycle. The PWM detector block measures the duty cycle at the PWM pin and uses this 16-bit value to generate an internal to the device PWM data. Before the output is generated, the PWM data goes through the PWM Curve Shaper block. Then, the data goes into the Adaptive Dimming function which determines the range of the PWM and Current control as described in OUTPUT DIMMING SCHEMES. The outcome of the Adaptive Dimming function is 12-bit Current and / or up to 6 PWM output signals. The current is then passed through the non-linear compensation block while the output PWM signals are channeled through the Dither block.

BRT MODE = 01

With BRT_MODE = 01, the PWM output is controlled by the PWM input duty cycle and the Brightness register. The PWM detector block measures the duty cycle at the PWM pin and uses this 16-bit value to generate the PWM data. Before the output is generated, the PWM data is first multiplied with BRT[7:0] register, then it goes through the PWM Curve Shaper block. Then, the data goes into the Adaptive Dimming function which determines the range of the PWM and Current control as described in OUTPUT DIMMING SCHEMES. The outcome of the Adaptive Dimming function is 12-bit Current and / or up to 6 PWM output signals. The current is then passed through the non-linear compensation block while the output PWM signals are channeled through the Dither block.

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BRT MODE = 10

With BRT_MODE = 10, the PWM output is controlled only by the Brightness register. From BRT[7:0] register, the data goes through the PWM Curve Shaper block. Then, the data goes into the Adaptive Dimming function which determines the range of the PWM and Current control as described in OUTPUT DIMMING SCHEMES. The outcome of the Adaptive Dimming function is 12-bit Current and / or up to 6 PWM output signals. The current is then passed through the non-linear compensation block while the output PWM signals are channeled through the Dither block.

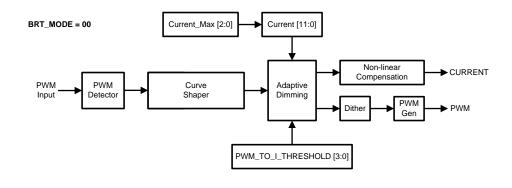
BRT_MODE = 11

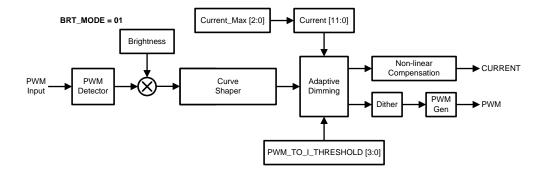
With BRT_MODE = 11, the PWM control signal path is similar to the path when BRT_MODE = 01 except that the PWM input signal is multiplied with BRT[7:0] data after the Curve Shaper block.

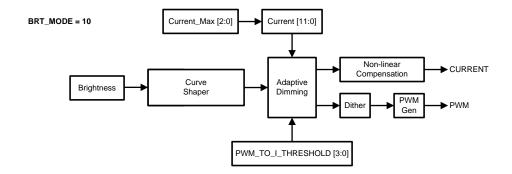
Table 2. Brightness Control Methods Truth Table

	•		
PWM_DIRECT	BRT_MODE [1:0]	Brightness Control Source	Output ILED Form
0	00	External PWM Signal	
0	01	External PWM Signal and Brightness Register (multiplied before Curve Shaper)	Adaptive. See OUTPUT
0	10	Brightness Register	DIMMING SCHEMES
0	11	External PWM Signal and Brightness Register (multiplied after Curve Shaper)	
1	don't care	External PWM Signal	Same as the external PWM input









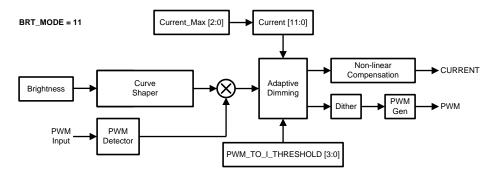


Figure 19. Brightness Control Signal Path Block Diagrams



OUTPUT DIMMING SCHEMES

The LP8556 supports three types of output dimming control methods: PWM Control, Pure Current Control and Adaptive Dimming (Hybrid PWM & Current) Control.

PWM Control

PWM control is the traditional way of controlling the brightness using PWM of the outputs with a same LED current across the entire brightness range. Brightness control is achieved by varying the duty cycle proportional to the input PWM. PWM frequency is set either using an external set Resistor (R_{FSET}) or using the PWM_FREQ EPROM field. The maximum LED current is set either using an external set Resistor (R_{ISET}) and CURRENT and CURRENT_MAX EPROM bits or just using the CURRENT and CURRENT_MAX EPROM bits. Note that the output PWM signal is de-coupled and generated independent of the input PWM signal eliminating display flicker issues and allowing better noise immunity

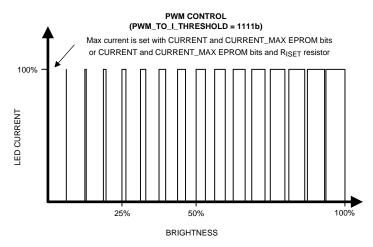


Figure 20. PWM Only Output Dimming Scheme

Pure Current Control

In Pure Current Control mode, brightness control is achieved by changing the LED current proportionately from maximum value to a minimum value across the entire brightness range. Like in PWM Control mode, the maximum LED current is set either using an external set Resistor (R_{ISET}) and CURRENT and CURRENT_MAX EPROM bits or just using the CURRENT and CURRENT_MAX EPROM bits. Current resolution in this mode is 12-bits.

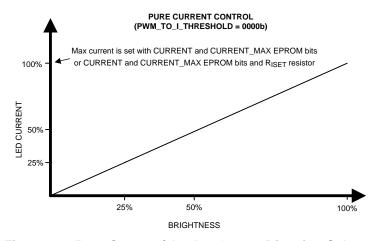


Figure 21. Pure Current / Analog Output Dimming Scheme



Adaptive Control

Adaptive dimming control combines PWM Control and Pure Current Control dimming methods. With the adaptive dimming, it is possible to achieve better optical efficiency from the LEDs compared to pure PWM control while still achieving smooth and accurate control at low brightness levels. Current resolution in this mode is 12-bits. Switch point from Current to PWM control can be set with the PWM_TO_I_THRESHOLD EPROM field from 0% to 100% of the brightness range to get good compromise between good matching of the LEDs brightness/white point at low brightness and good optical efficiency.

PWM frequency is set either using an external set Resistor (R_{FSET}) or using the PWM_FREQ EPROM bits. The maximum LED current is set either using an external set Resistor (R_{ISET}) and CURRENT and CURRENT_MAX EPROM bits or just using the CURRENT and CURRENT_MAX EPROM bits.

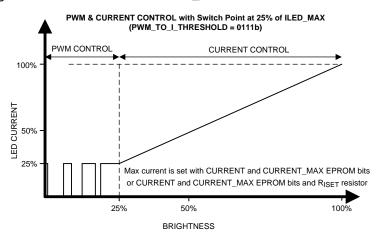


Figure 22. Adaptive Output Dimming Scheme

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SETTING FULL-SCALE LED CURRENT

The maximum or full scale LED current is set either using an external set Resistor (R_{ISET}) and CURRENT and CURRENT_MAX EPROM bits or just using the CURRENT and CURRENT_MAX EPROM bits. Table 3 summarizes setting of the full scale LED current.

Table 3. Setting Full-Scale LED Current

R _{ISET} [Ω]	ISET_EN	CURRENT_MAX	CURRENT[11:0]	Full Scale ILED [mA]
don't care	0	000	FFFh	5
don't care	0	001	FFFh	10
don't care	0	010	FFFh	15
don't care	0	011	FFFh	20
don't care	0	100	FFFh	23
don't care	0	101	FFFh	25
don't care	0	110	FFFh	30
don't care	0	111	FFFh	50
don't care	0	000 - 111	001h - FFFh	(1)
24k	1	000	FFFh	5
24k	1	001	FFFh	10
24k	1	010	FFFh	15
24k	1	011	FFFh	20
24k	1	100	FFFh	23
24k	1	101	FFFh	25
24k	1	110	FFFh	30
24k	1	111	FFFh	50
12k - 100k	1	000 - 111	001h - FFFh	(1)

⁽¹⁾ See CFG0



SETTING PWM DIMMING FREQUENCY

LP8556 PWM dimming frequency can be set either by an external resistor, R_{FSET} , or by pre-configuring EPROM Memory (CFG5 register, PWM_FREQ[3:0] bits). Table 4 summarizes setting of the PWM dimming frequency. Note that the R_{FSET} is shared for setting the boost switching frequency, too. Setting the boost switching frequency and PWM dimming frequency using an external resistor is shown in Table 5.

Table 4. Configuring PWM Dimming Frequency via EPROM

R _{FSET} [kΩ]	PWM_FSET_EN	PWM_FREQ[3:0]	f _{PWM} [Hz] (Resolution)
		0000	4808 (12-bit)
		0001	6010 (11-bit)
		0010	7212 (11-bit)
		0011	8414 (11-bit)
		0100	9616 (11-bit)
		0101	12020 (10-bit)
		0110	13222 (10-bit)
don't core	0	0111	14424 (10-bit)
don't care	0	1000	15626 (10-bit)
		1001	16828 (10-bit)
		1010	18030 (10-bit)
		1011	19232 (10-bit)
		1100	24040 (9-bit)
		1101	28848 (9-bit)
		1110	33656 (9-bit)
		1111	38464 (9-bit)
(1)	1	don't care	(1)

(1) See Table 5



Table 5. Setting Switching and PWM Dimming Frequency with an External Resistor

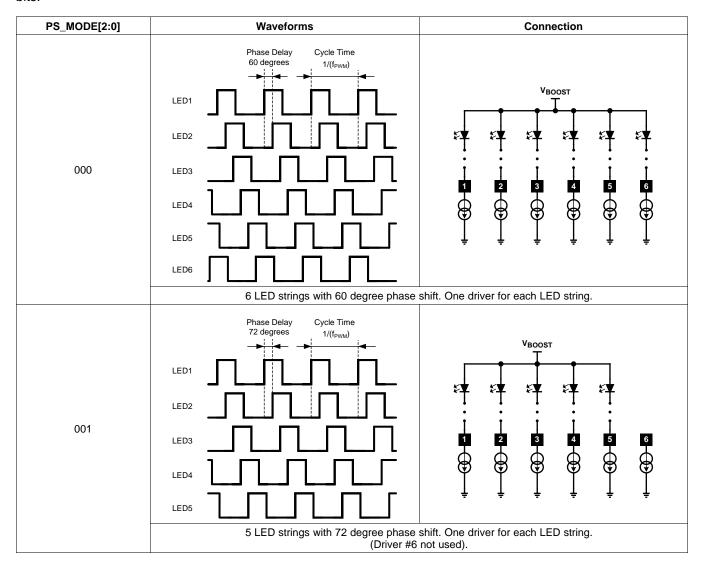
R _{FSET} [kΩ] (Tolerance)	f _{SW} [kHz]	f _{PWM} [Hz] (Resolution)
Floating or FSET pin pulled HIGH	1250	9616 (11-bit)
470k - 1M (±5%)	312	2402 (12-bit)
300k, 330k (±5%)	312	4808 (12-bit)
200k (±5%)	312	6010 (11-bit)
147k, 150k, 154k, 158k (±1%)	312	9616 (11-bit)
121k (±1%)	312	12020 (10-bit)
100k (±1%)	312	14424 (10-bit)
86.6k (±1%)	312	16828 (10-bit)
75.0k (±1%)	312	19232 (10-bit)
63.4k (±1%)	625	2402 (12-bit)
52.3k, 53.6k (±1%)	625	4808 (12-bit)
44.2k, 45.3k (±1%)	625	6010 (11-bit)
39.2k (±1%)	625	9616 (11-bit)
34.0k (±1%)	625	12020 (10-bit)
30.1k (±1%)	625	14424 (10-bit)
26.1k (±1%)	625	16828 (10-bit)
23.2k (±1%)	625	19232 (10-bit)
20.5k (±1%)	1250	2402 (12-bit)
18.7k (±1%)	1250	4808 (12-bit)
16.5k (±1%)	1250	6010 (11-bit)
14.7k (±1%)	1250	9616 (11-bit)
13.0k (±1%)	1250	12020 (10-bit)
11.8k (±1%)	1250	14424 (10-bit)
10.7k (±1%)	1250	16828 (10-bit)
9.76k (±1%)	1250	19232 (10-bit)
FSET pin shorted to GND	1250	Same as PWM input



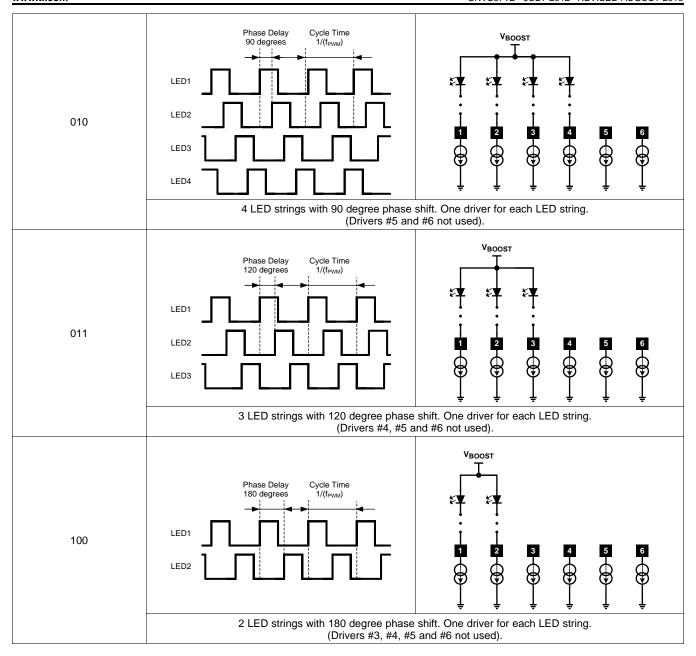
PHASE SHIFT PWM SCHEME

Phase shift PWM scheme allows delaying the time when each LED driver is active. When the LED drivers are not activated simultaneously, the peak load current from the boost output is greatly decreased. This reduces the ripple seen on the boost output and allows smaller output capacitors. Reduced ripple also reduces the output ceramic capacitor audible ringing. PSPWM scheme also increases the load frequency seen on the boost output six times and therefore transfers the possible audible noise to the frequencies outside of the audible range.

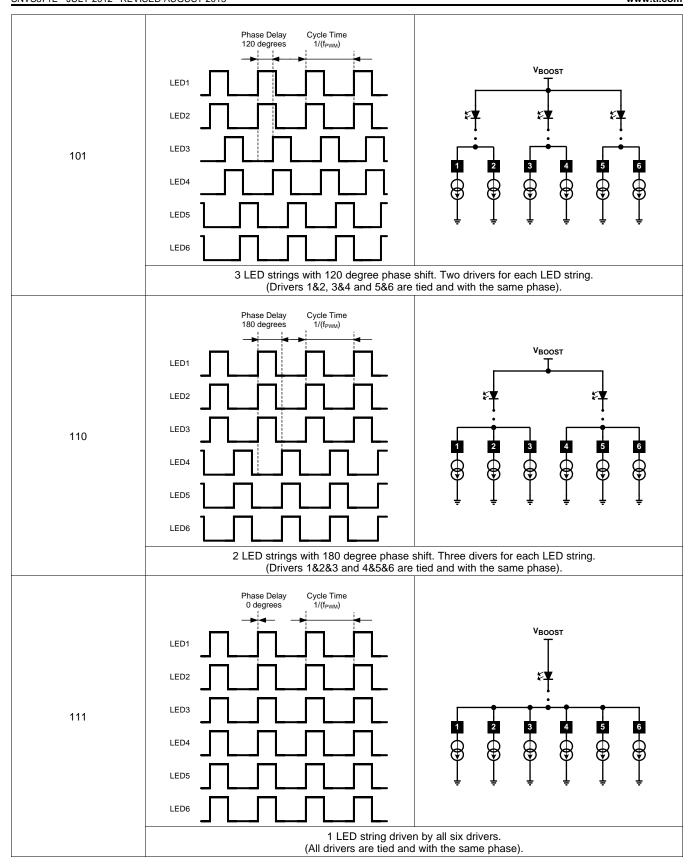
Description of the PSPWM mode is seen in the following diagrams. PSPWM mode is set with <PS_MODE[2:0]> bits.



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SLOPE AND ADVANCED SLOPE

Transition time between two brightness values can be programmed with EPROM bits <PWM_SLOPE[2:0]> from 0 to 500 ms. Same slope time is used for sloping up and down. With advanced slope the brightness changes can be made more pleasing to a human eye.

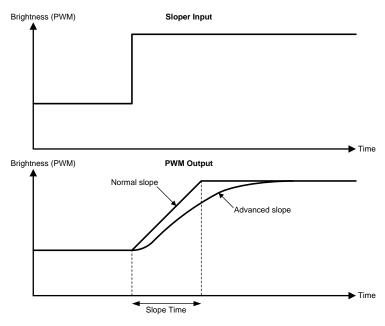


Figure 23. Sloper Operation

DITHERING

Special dithering scheme can be used during brightness changes and in steady state condition. It allows increased resolution and smaller average steps size during brightness changes. Dithering can be programmed with EPROM bits <DITHER[1:0]> from 0 to 3 bits. <STEADY_DITHER> EPROM bit sets whether the dithering is used also in steady state or only during slopes. Example below is for 1-bit dithering. E.g. for 3-bit dithering, every 8th pulse is made 1 LSB longer to increase the average value by 1/8th.

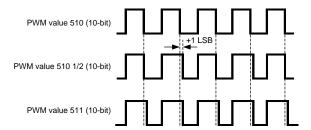


Figure 24. Example of the Dithering, 1-bit dither, 10-bit resolution



Fault Detection

LP8556 has fault detection for LED open and short conditions, UVLO, over-current and thermal shutdown. The cause for the fault can be read from status register. Reading the fault register will also reset the fault.

LED FAULT DETECTION

With LED fault detection, the voltages across the LED drivers are constantly monitored. Shorted or open LED strings are detected.

OPEN DETECT: The logic uses the LOW comparators and the requested boost voltage to detect the OPEN condition. If the logic is asking the boost for the maximum allowed voltage and a LOW comparator is asserted, then the OPEN bit is set in the STATUS register (ADDR=02h). In normal operation, the adaptive headroom control loop raises the requested boost voltage when the LOW comparator is asserted. If it has raised it as high as it can and an LED string still needs more voltage, then it is assumed to be disconnected from the boost voltage (open or grounded). The actual boost voltage is not part of the OPEN condition decision; only the requested boost voltage and the LOW comparators.

SHORT DETECT: The logic uses all three comparators (HIGH, MID and LOW) to detect the SHORT condition. When the MID and LOW comparators are de-asserted, the headroom control loop considers that string to be optimized - enough headroom, but not excessive. If at least one LED string is optimized and at least one other LED string has its HIGH comparator asserted, then the SHORT condition is detected. It is important to note that the SHORT condition requires at least two strings for detection: one in the optimized headroom zone (LOW/MID/HIGH comparators all de-asserted) and one in the excessive headroom zone (HIGH comparator asserted).

Fault is cleared by reading the fault register.

UNDER-VOLTAGE DETECTION

LP8556 has detection for too-low VIN voltage. Threshold level for the voltage is set with EPROM register bits as shown in the following table:

 UVLO_EN
 UVLO_TH
 Threshold (V)

 0
 don't care
 OFF

 1
 0
 2.5V

 1
 1
 5.2V

Table 6. UVLO Truth Table

When under voltage is detected the LED outputs and the boost will shutdown and the corresponding fault bit is set in the fault register. The LEDs and the boost will start again when the voltage has increased above the threshold level. Hysteresis is implemented to threshold level to avoid continuous triggering of fault when threshold is reached.

Fault is cleared by setting the EN / VDDIO pin low or by reading the fault register.

OVER-CURRENT PROTECTION

LP8556 has detection for too-high loading on the boost converter. When over-current fault is detected, the the boost will shutdown and the corresponding fault bit is set in the fault register. The boost will start again when the current has dropped below the OCP threshold.

Fault is cleared by reading the fault register.

THERMAL SHUTDOWN

If the LP8556 reaches thermal shutdown temperature (150 $^{\circ}$ C) the LED outputs and boost will shut down to protect it from damage. Device will re-activate again when temperature drops below 130 $^{\circ}$ C degrees.

Fault is cleared by reading the fault register.



I²C-Compatible Serial Bus Interface

INTERFACE BUS OVERVIEW

The I²C-compatible synchronous serial interface provides access to the programmable functions and registers on the device. This protocol uses a two-wire interface for bidirectional communications between the IC's connected to the bus. The two interface lines are the Serial Data Line (SDA) and the Serial Clock Line (SCL). These lines should be connected to a positive supply via a pull-up resistor and remain HIGH even when the bus is idle.

Every device on the bus is assigned a unique address and acts as either a Master or a Slave depending on whether it generates or receives the SCL. The LP8556 can operate as an I²C slave.

DATA TRANSACTIONS

One data bit is transferred during each clock pulse. Data is sampled during the high state of the serial clock SCL. Consequently, throughout the clock's high period, the data should remain stable. Any changes on the SDA line during the high state of the SCL and in the middle of a transaction, aborts the current transaction. New data should be sent during the low SCL state. This protocol permits a single data line to transfer both command/control information and data using the synchronous serial clock.

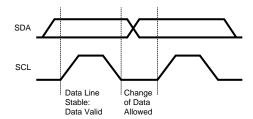


Figure 25. Bit Transfer

Each data transaction is composed of a Start Condition, a number of byte transfers (set by the software) and a Stop Condition to terminate the transaction. Every byte written to the SDA bus must be 8 bits long and is transferred with the most significant bit first. After each byte, an Acknowledge signal must follow. The following sections provide further details of this process.

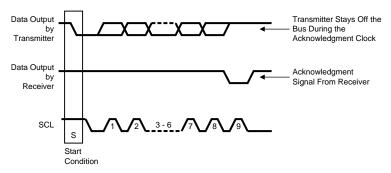


Figure 26. Start and Stop

The Master device on the bus always generates the Start and Stop Conditions (control codes). After a Start Condition is generated, the bus is considered busy and it retains this status until a certain time after a Stop Condition is generated. A high-to-low transition of the data line (SDA) while the clock (SCL) is high indicates a Start Condition. A low-to-high transition of the SDA line while the SCL is high indicates a Stop Condition.



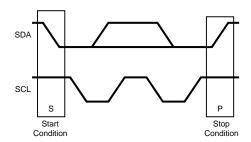


Figure 27. Start and Stop Conditions

In addition to the first Start Condition, a repeated Start Condition can be generated in the middle of a transaction. This allows another device to be accessed, or a register read cycle.

ACKNOWLEDGE CYCLE

The Acknowledge Cycle consists of two signals: the acknowledge clock pulse the master sends with each byte transferred, and the acknowledge signal sent by the receiving device.

The master generates the acknowledge clock pulse on the ninth clock pulse of the byte transfer. The transmitter releases the SDA line (permits it to go high) to allow the receiver to send the acknowledge signal. The receiver must pull down the SDA line during the acknowledge clock pulse and ensure that SDA remains low during the high period of the clock pulse, thus signaling the correct reception of the last data byte and its readiness to receive the next byte.

"ACKNOWLEDGE AFTER EVERY BYTE" RULE

The master generates an acknowledge clock pulse after each byte transfer. The receiver sends an acknowledge signal after every byte received.

There is one exception to the "acknowledge after every byte" rule. When the master is the receiver, it must indicate to the transmitter an end of data by not-acknowledging ("negative acknowledge") the last byte clocked out of the slave. This "negative acknowledge" still includes the acknowledge clock pulse (generated by the master), but the SDA line is not pulled down.

ADDRESSING TRANSFER FORMATS

Each device on the bus has a unique slave address. The LP8556 operates as a slave device with 7-bit address combined with data direction bit. Slave address is 2Ch as 7-bit or 58h for write and 59h for read in 8-bit format.

Before any data is transmitted, the master transmits the the slave I.D. The slave device should send an acknowledge signal on the SDA line, once it recognizes its address.

The slave address is the first seven bits after a Start Condition. The direction of the data transfer (R/W) depends on the bit sent after the slave address — the eighth bit.

When the slave address is sent, each device in the system compares this slave address with its own. If there is a match, the device considers itself addressed and sends an acknowledge signal. Depending upon the state of the R/W bit (1:read, 0:write), the device acts as a transmitter or a receiver.



Figure 28. I²C Chip Address (0x2C)

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Control Register Write Cycle

- Master device generates start condition.
- Master device sends slave address (7 bits) and the data direction bit (r/w = 0).
- Slave device sends acknowledge signal if the slave address is correct.
- Master sends control register address (8 bits).
- Slave sends acknowledge signal.
- · Master sends data byte to be written to the addressed register.
- Slave sends acknowledge signal.
- If master will send further data bytes the control register address will be incremented by one after acknowledge signal.
- Write cycle ends when the master creates stop condition.

Control Register Read Cycle

- · Master device generates a start condition.
- Master device sends slave address (7 bits) and the data direction bit (r/w = 0).
- Slave device sends acknowledge signal if the slave address is correct.
- Master sends control register address (8 bits).
- · Slave sends acknowledge signal.
- · Master device generates repeated start condition.
- Master sends the slave address (7 bits) and the data direction bit (r/w = 1).
- Slave sends acknowledge signal if the slave address is correct.
- Slave sends data byte from addressed register.
- If the master device sends acknowledge signal, the control register address will be incremented by one. Slave
 device sends data byte from addressed register.
- Read cycle ends when the master does not generate acknowledge signal after data byte and generates stop condition.

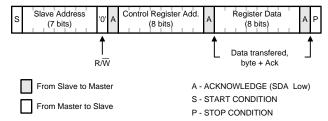
Table 7. Data Read and Write Cycles

	Address Mode
Data Read	<start condition=""> <slave address=""><r w="0">[Ack] <register addr.="">[Ack] <repeated condition="" start=""> <slave address=""><r w="1">[Ack] [Register Data]<ack nack="" or=""> additional reads from subsequent register address possible <stop condition=""></stop></ack></r></slave></repeated></register></r></slave></start>
Data Write	<start condition=""> <slave address=""><r w="0">[Ack] <register addr.="">[Ack] <register data="">[Ack] additional writes to subsequent register address possible <stop condition=""></stop></register></register></r></slave></start>

<>Data from master [] Data from slave



Register Read and Write Detail



Register Write Format

Figure 29. Register Write Format

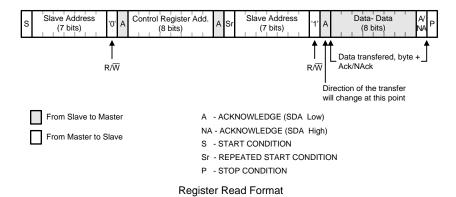


Figure 30. Register Read Format

Product Folder Links: LP8556

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Table 8. Register Map

ADD R	REGISTER	D7	D6	D5	D4	D3	D2	D1	D0	RESET
H00	Brightness Control		BRT[7:0]							
01H	Device Control	FAST					BRT_	MODE	BL_CTL	0000 0000
02H	Status	OPEN	SHORT	VREF_OK	VBOOST_ OK	OVP	OCP	TSD	UVLO	0000 0000
03H	D	PANEL	MFG REV						1111 1100	
04H	Direct Control			LED					0000 0000	
16H	LED Enable			LED_EN						0011 1111

Table 9. EPROM Memory Map

ADD R	REGISTER	D7	D6	D5	D4	D3	D2	D1	D0	
98H	CFG98	IBOOST_LIM_ 2X		RESERVED			RES	SERVED		
9EH	CFG9E	RESERV	ED	VBOOST_RA NGE	RESERVE D		HEADRO	OM_OFFSET		
A0H	CFG0				CURF	RENT LSB				
A1H	CFG1	PDET_STDBY		CURRENT_MA	·Χ		CURF	RENT MSB		
A2H	CFG2	RESERV	ED	UVLO_EN	UVLO_TH	BL_ON	ISET_EN	BOOST_FSET _EN	PWM_FSET_ EN	
АЗН	CFG3	RESERVED		SLOPE		FII	LTER	PWM_INPUT_I	HYSTERESIS	
A4H	CFG4	P.	WM_TO_I	I_THRESHOLD RESERVE STEADY_DIT DITHER D HER				IER		
A5H	CFG5	PWM_DIRECT		PS_MODE			PWI	M_FREQ		
A6H	CFG6	BOOST_F	REQ			V	BOOST	OOST		
A7H	CFG7	RESERV	ED	EN_DRV3	EN_DRV2	RES	ERVED	IBOOS	T_LIM	
A8H	CFG8	RESERV	ED	RESER	VED	RESERVED		RESERVED		
A9H	CFG9	VE	OOST_M	AX	JUMP_EN	JUMP_T	HRESHOLD	JUMP_V	OLTAGE	
AAH	CFGA	SSCLK_EN	RESER VED	RESER	VED	ADAPTIV E	DR	RIVER_HEADRO	MC	
ABH	CFGB				RES	SERVED				
ACH	CFGC		RES	ERVED			RESERVED			
ADH	CFGD				RES	SERVED				
AEH	CFGE	STEP_U	IP	STEP_DN LED_FAULT				LED_COM	IP_HYST	
AFH	CFGF				RE	VISION				

Product Folder Links: LP8556



Register Bit Explanations

BRIGHTNESS CONTROL

Address 00h

Reset value 0000 0000b

Brightness Control register											
7	6 5 4 3 2 1 0										
	BRT[7:0]										
Name	Bit	Access	Description	Description							
BRT	7:0	R/W	Backlight PWM 8-bit linear control.								

DEVICE CONTROL

Address 01h

Reset value 0000 0000b

Device Control I	register								
7	6	5	4	3	2	1	0		
FAST					BRT_	MODE[1:0]	BL_CTL		
Name	Bit	Access	Description						
FAST	7		Skip refresh of power STAND 0 = read EPRO 1 = only read I	BY mode. DMs before re	eturning to the	ACTIVE state	As when exiting the low		
BRT_MODE	2:1 F	2:1 R/W	R/W Brightness source mode Figure 19						
					00b = PWM input only				
			01b = PWM input and Brightness register (combined before shaper block)						
			10b = Brightness register only						
			11b = PWM input and Brightness register (combined after shaper blo						
BL_CTL	0	(BRT_MODE = 1 0 = Backlight disa	R/W	Enable backlight when Brightness Register is used to control brightness (BRT_MODE = 10).					
			acklight disabled and chip turned off acklight enabled and chip turned on						
							brightness control ole or disables the chip.		

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STATUS

Address 02h

Reset value 0000 0000b

Fault register									
7	6	5	4	3	2	1	0		
OPEN	SHORT	VREF_OK	VBOOST_OK	OVP	OCP	TSD	UVLO		
Name	Bit	Access	Description						
OPEN	7	R	LED open fault detection						
			0 = No fault						
			1 = LED open fault de	tected. The value	is not latched.				
SHORT	6	R	LED short fault detecti	on					
			0 = No fault						
			1 = LED short fault de	tected. The value	is not latched.				
VREF_OK	5	R	Internal VREF node m	onitor status					
			1 = VREF voltage is C	K.					
VBOOST_OK	4	R	Boost output voltage n	nonitor status					
			0 = Boost output volta	ge has not reache	ed its target (VBO	OST < Vtarget	- 2.5V)		
			1 = Boost output volta	ge is OK. The valu	ue is not latched.				
OVP	3 R Overvoltage protection								
	0 = No fault								
			1 = Overvoltage condi	tion occurred. Fau	ılt is cleared by re	eading the regis	ter 02h.		
OCP	2	R	Over current protection						
			0 = No fault						
			1 = Over current detection output and if the boost OCP fault and disable clearing the fault boost	output has been the boost. Fault is	too low for more s cleared by read	than 50 ms it w	ill generate		
TSD	1	R	Thermal shutdown						
			0 = No fault						
			1 = Thermal fault gene disabled until the temp this register.						
UVLO	0	R	Under voltage detection						
			0 = No fault						
			1 = Under-voltage dete disabled until V _{DD} volta set with EPROM bits.	age is above the l	JVLO threshold v	oltage. Thresho			

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IDENTIFICATION

Address 03h

Reset value 1111 1100b

Identification register								
7	6	5	4	3	2	1	0	
PANEL	MFG[3:0]			REV[2:0]				
Name	Bit	Access	Description					
PANEL	7	R	Panel ID code					
MFG	6:3	R	Manufacturer ID code					
REV	2:0	R	Revision ID code					

DIRECT CONTROL

Address 04h

Reset value 0000 0000b

Direct Control regis	ster							
7	6	5	4	3	2	1	0	
		OUT[5:0]						
Name	Bit	Access	Description					
OUT	5:0	R/W	R/W Direct control of the LED outputs 0 = Normal operation. LED output are controlled with the adaptive dimming block 1 = LED output is forced to 100% PWM.					

LED String Enable

Address 16h

Reset value 0011 1111b

Temp LSB register									
7	6	5	4	3	2	1	0		
		LED_EN[5:0]							
Name	Bit	Access	Description						
LED_EN	5:0	R/W	Bits 5:0 correspond to LED Strings 6:1 respectively. Bit value 1 = LED String Enabled Bit value 0 = LED String Disabled Note: To disable string(s), it is recommended to disable higher order string(s). For example, - for 5-String configuration, disable 6th String. For 4-string configuration, disable 6th and 5th string. These bits are ANDed with the internal LED enable bits that are generated with the PS_MODE logic.						



EPROM Bit Explanations

LP8556TM (DSBGA) Configurations and Pre-configured EPROM Settings

ADDRESS	LP8556-E00	LP8556-E01	LP8556-E02	LP8556-E03	LP8556-E04	LP8556-E05 (1)	LP8556-E06
98h[7]	0b	0b	0b	0b	0b	0b	0b
9Eh	22h	22h	22h	24h	24h	22h	22h
A0h	FFh	FFh	FFh	FFh	FFh		FFh
A1h	CFh	4Fh	5Fh	BFh	3Fh		DBh
A2h	2Fh	20h	20h	28h	2Fh		2Fh
A3h	5Eh	03h	5Eh	5Eh	5Eh		02h
A4h	72h	12h	72h	72h	72h		72h
A5h	14h	0Ch	04h	14h	04h		14h
A6h	80h	80h	80h	80h	80h		40h
A7h	FFh	FFh	FFh	FFh	FFh		F7h
A8h	00h	00h	00h	00h	00h		20h
A9h	A0h	80h	80h	A0h	60h		DBh
AAh	0Fh	0Fh	0Fh	0Fh	0Fh		0Fh
ABh	00h	00h	00h	00h	00h		00h
ACh	00h	00h	00h	00h	00h		00h
ADh	00h	00h	00h	00h	00h		00h
AEh	0Fh	0Fh	0Fh	0Fh	0Fh		0Fh
AFh	02h	02h	04h	02h	02h		04h

⁽¹⁾ LP8556-E05 is a device option with un-configured EPROM settings. This option is for users that desire programming the device by themselves. Bits 98h[7] and 9Eh[5] are always pre-configured.

LP8556TM (DSBGA) Configurations and Pre-configured EPROM Settings Continued

ADDRESS	LP8556-E07	LP8556-E08	LP8556-E09	LP8556-E10	LP8556-E11	LP8556-E12	LP8556-E13
98h[7]	0b						
9Eh	04h	22h	22h	24h	02h	04h	22h
A0h	FFh	FFh	FFh	EBh	FFh	FFh	FFh
A1h	BFh	CFh	CFh	3Dh	4Fh	3Fh	DBh
A2h	0Dh	2Fh	2Fh	2Fh	20h	2Fh	2Fh
A3h	02h	5Eh	02h	37h	03h	02h	02h
A4h	72h	72h	72h	77h	12h	72h	72h
A5h	20h	24h	04h	1Bh	3Ch	14h	24h
A6h	4Eh	80h	80h	40h	40h	40h	40h
A7h	FEh	FFh	F7h	FEh	F8h	FBh	F7h
A8h	21h	00h	04h	21h	20h	00h	20h
A9h	C0h	A0h	A0h	9Bh	80h	C0h	DBh
AAh	0Fh	0Fh	0Fh	3Fh	0Fh	0Fh	0Fh
ABh	00h						
ACh	00h						
ADh	00h						
AEh	0Fh	0Fh	0Eh	0Fh	0Fh	0Eh	0Fh
AFh	02h	02h	05h	00h	00h	00h	00h



LP8556SQ (WQFN) Configurations and Pre-configured EPROM Settings

ADDRESS	LP8556-E00	LP8556-E08	LP8556-E09
98h[7]	1b	1b	1b
9Eh	22h	22h	22h
A0h	FFh	FFh	FFh
A1h	CFh	CFh	CFh
A2h	2Fh	2Fh	2Fh
A3h	5Eh	5Eh	02h
A4h	72h	72h	72h
A5h	14h	24h	04h
A6h	80h	80h	80h
A7h	FEh	FEh	FEh
A8h	00h	00h	00h
A9h	A0h	A0h	A0h
AAh	0Fh	0Fh	0Fh
ABh	00h	00h	00h
ACh	00h	00h	00h
ADh	00h	00h	00h
AEh	0Fh	0Fh	0Fh
AFh	00h	00h	00h

CFG98

Address 98h

CFG98 register							
7	6	5	4	3	2	1	0
IBOOST_LIM_2X							
Name	Bit	Access			Description		
IBOOST_LIM_2X	7	R/W	When IBOOST_LIM	_2X = 0, the inc _2X = 1, the inc	ge. ductor current limit car ductor current limit car package and not on D	n be set to 1.6A, 2	.1A, or 2.6A . This

^{(1) 1.8}A is the maximum I_{SW_LIM} supported with the DSBGA package. For applications requiring the I_{SW_LIM} to be greater than 1.8A and up to 2.6A, WQFN package should be considered.

CFG9E

Address 9Eh

CFG9E register									
7	6	5	4	3	2	1	0		
		VBOOST_RANGE	HEADROOM_OFFSET						
Name	Bit	Access	Description						
VBOOST_RANGE	5	R/W	Select VBOOST range. When VBOOST_RANGE = 0, the output voltage range is from 7V to 34V When VBOOST_RANGE = 1, the output voltage range is from 16V to 43V						
HEADROOM_ OFFSET	3:0	R/W		EADROOM bit mV mV mV mV	t. This adjusts the LO' s and contributes to th				

CFG0

Address A0h

CFG0 register										
7	6	5	4	3	2	1	0			
			CURRE	NT LSB[7:0]	·					
Name	Bit	Access			Description					
CURRENT LSB	7:0	R/W	LED current to be current set using 0, the LED currer	The 8-bits in this register (LSB) along the 4-bits defined in CFG1 Register (MSB) allow LED current to be set in 12-bit fine steps. These 12-bits further scale the maximum LED current set using CFG1 Register, CURRENT_MAX bits (denoted as IMAX). If ISET_EN = 0, the LED current is defined with the bits as shown below. If ISET_EN = 1, then the external resistor connected to the ISET pin scales the LED current as shown below.						
					ISET_EN = 0	ISET_E	N = 1			
			0000	0000 0000	0A	0A				
			0000	0000 0001	(1/4095) x I _{MAX}	(1/4095) x I _{MAX} x R _{ISE}				
			0000	0000 0010	(2/4095) x I _{MAX}	(2/4095) x I _{MAX} x R _{ISE}				
			0111	1111 1111	(2047/4095) x I _{MAX}	(2047/4095) x I _N 1.2V / I				
			1111	1111 1101	(4093/4095) x I _{MAX}	(4093/4095) x I _N 1.2V / I				
			1111	1111 1110	(4094/4095) x I _{MAX}	(4094/4095) x I _N 1.2V / I	MAX X 20000 X RISET			
			1111	1111 1111	(4095/4095) x I _{MAX}	(4095/4095) x I _N 1.2V / I	MAX x 20000 x RISET			

CFG1

Address A1h

CFG1 register									
7	6	5	4	3	2	1	0		
PDET_STDBY	C	URRENT_MAX	[2:0]		CURREN	T MSB[11:8]			
Name	Bit	Access	Description						
PDET_STDBY	7	R/W	Enable Standb	y when PWM in	nput is constant low (approx. 50 ms time	eout).		
CURRENT_MAX	6:4	R/W		LED current as le CFG0 Regist	shown below. This ner.	naximum current is	scaled as		
CURRENT MSB	3:0	R/W	These bits form	n the 4 MSB bit	s for LED Current as	described in CFG0	Register		

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CFG2

Address A2h

CFG2 register							
7	6	5	4	3	2	1	0
RESERVED		UVLO_EN	UVLO_TH	BL_ON	ISET_EN	BOOST_ _FSET_EN	PWM_ _FSET_EN
Name	Bit	Access	Description				
RESERVED	7:6	R/W					
UVLO_EN	5	R/W	Undervoltage I	ockout protecti	on enable.		
UVLO_TH	4	R/W	UVLO threshol 0 = 2.5V 1 = 5.2V	d levels:			
BL_ON	3	R/W	0 = Backlight d master. With a register 01h.	lisabled. This s n I2C master, t	he backlight car	mmended for sys	stems with an I2C y writing to the tems with PWM
ISET_EN	2	R/W	EPROM registe 1 = Resistor is	disabled and cer bits. enabled and c	urrent is set wit	n the R _{ISET} resis	d CURRENT_MAX
BOOST_FSET_EN	1	R/W	0 = Configurati switching frequ	on of the switc lency is set wit	hing frequency on BOOST_FRE	cy via FSET pin. via FSET pin is i Q EPROM regist via FSET pin is i	s disabled. The er bits.
PWM_FSET_EN	0	R/W	0 = Configurati switching frequ	on of the switc lency is set wit	hing frequency v h PWM_FREQ I	equency via FSE via FSET pin is i EPROM register ency via FSET p	s disabled. The bits.

CFG3

40

Address A3h

3 register							
7	6	5	4	3	2	1	0
RESERVED		SLOPE[2:0]]	FILT	ER[1:0]	PWM_INPUT	_HYSTERESIS[1:0]
Name	Bit	Access	Description				
RESERVED	7	R/W					
SLOPE	6:4	R/W				n	
FILTER	3:2	R/W	Select brightn 00 = No filterin 01 = light smo 10 = medium 11 = heavy sn	othing smoothing	nsition filtering	strength	
PWM_INPUT_ _HYSTERESIS	1:0	R/W	00 = OFF 01 = 1-bit hys 10 = 1-bit hys	steresis function teresis with 13- teresis with 12- teresis with 8-b	bit resolution bit resolution		

CFG4

Address A4h

CFG4 register								
7	6	5	4	3	2	1	0	
PWM_	TO_I_THRE	SHOLD[3:0]		RESERVED	STEADY_ _DITHER	DIT	HER[1:0]	
Name	Bit	Access	Description					
PWM_TO_I_THRESHOL D	7:4	R/W	0000 = curre 0001 = switc 0010 = switc 0011 = switc 0100 = switc 0101 = switc 0110 = switc 0111 = switc 1000 = switc 1001 = switc 1001 = switc	n point between Fent dimming across hopoint at 10% of the point at 12.5% of the point at 17.5% of the point at 22.5% of the point at 22.5% of the point at 23.33% of the point at 33.33% of the point at 41.67% of the point at 50% of the point at 50	ss entire range if the maximum L of the maximum L to of the maximum L to the maximum L to the maximum L	ED current. LED current. LED current. LED current. ED current. LED current. LED current. The current. LED current. LED current. LED current.	is is a	
RESERVED	3	R/W						
STEADY_DITHER	2	R/W		on method select nly on transitions all times	:			
DITHER	1:0	R/W	Dither function control 00 = Dithering disabled 01 = 1-bit dithering 10 = 2-bit dithering 11 = 3-bit dithering					



CFG5

Address A5h

7	6	5	4	3	2	1	0	
PWM_DIRECT		PS_MODE[2:0)]		PWM_	FREQ[3:0]		
Name	Bit	Access	Description					
PWM_DIRECT	7	R/W	Intended for certain test mode purposes. When enabled, the entire pipeline bypassed and PWM output is connected with PWM input.					
PS_MODE	6:4	R/W	001 = 5-phase 010 = 4-phase 011 = 3-phase 100 = 2-phase 101 = 3-phase 110 = 2-phase	, 6 drivers (0°, , 5 drivers (0°, , 4 drivers (0°, , 3 drivers (0°, , 2 drivers (0°, , 6 drivers (0°, , 6 drivers (0°,	nfiguration: 60°, 120°, 180°, ; 72°, 144°, 216°, , 90°, 180°, 270°, , 120°, 240°, OFF, 180°, OFF, OFF, 0°, 120°, 120°, 2 0°, 0°, 180°, 180 0°, 0°, 0°, 0°, 0°, 0°,	288°, OFF) OFF, OFF) OFF, OFF) OFF, OFF) 40°, 240°)		
PWM_FREQ	3:0	R/W	0h = 4,808 Hz 1h = 6,010 Hz 2h = 7,212 Hz 3h = 8,414 Hz 4h = 9,616 Hz 5h = 12,020 Hz 6h = 13,222 Hz 7h = 14,424 Hz 8h = 15,626 Hz 9h = 16,828 Hz Ah = 18,030 Hz Bh = 19,232 Hz Ch = 24,040 Hz Dh = 28,848 Hz Eh = 33,656 Hz Fh = 38,464 Hz	(10-bit) (10-bit) (10-bit) (10-bit) z (9-bit) z (9-bit) z (9-bit) z (9-bit) z (9-bit) z (9-bit) z (9-bit) z (8-bit) z (8-bit) z (8-bit)				

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CFG6

Address A6h

CFG6 register											
7	6	5	4 3 2 1 0								
BOOST_FREQ[1:0]			VBOO	ST[5:0]						
Name	Bit	Access	Description								
BOOST_FREQ	7:6	R/W	Set boost switch 00 = 312 kHz 01 = 625 kHz 10 = 1250 kHz 11 = undefined	ning frequenc	y when BOOST_	_FSET_EN = 0.					
VBOOST	5:0	R/W	Boost output vo initial voltage.	Itage. When /	ADAPTIVE = 1, 1	this is the boost i	minimum and				

CFG7

Address A7h

7	6	5	4	3	2	1	0	
RESERVED)	EN_DRV3	EN_DRV2	EN_DRV2 RESERVED				
Name	Bit	Access	Description					
RESERVED	7:6							
EN_DRV3	5	R/W	Selects boost dr section for more 0 = Driver3 disal 1 = Driver3 enab	detail. oled	to set boost slev	w rate. See EMI	REDUCTION	
EN_DRV2	4	R/W	Selects boost dr section for more 0 = Driver2 disal 1 = Driver2 enab	detail. oled	to set boost slev	w rate. See EMI	REDUCTION	
RESERVED	3:2	R/W						
IBOOST_LIM	1:0	R/W	Select boost ind (IBOOST_LIM_2 00 = 0.9A / 1.6A 01 = 1.2A / 2.1A 10 = 1.5A / 2.6A 11 = 1.8A / not p	X = 0 / IBOO)		

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CFG9

Address A9h

FG9 register										
7	6	5	4	3	2	1	0			
VBOO	ST_MAX[2:0]		JUMP_EN	JUMP_THE	ESHOLD[1:0]	JUMP_V	OLTAGE[1:0]			
Name	Bit	Access	Description							
VBOOST_MAX	7:5	R/W	Select the maximum boost voltage (typ values) (VBOOST_RANGE = 0 / VBOOST_RANGE = 1) 010 = NA / 21V 011 = NA / 25V 100 = 21V / 30V 101 = 25V / 34.5V 110 = 30V / 39V 111 = 34V / 43V							
JUMP_EN	4	R/W	Enable JUMP	detection on th	ne PWM input.					
JUMP_THRESHOLD	3:2	R/W	Select JUMP t 00 = 10% 01 = 30% 10 = 50% 11 = 70%	hreshold:						
JUMP_VOLTAGE	1:0	R/W	Select JUMP v 00 = 0.5V 01 = 1V 10 = 2V 11 = 4V	voltage:						

CFGA

Address AAh

GA register											
7	6	5	4	3	2	1	0				
SSCLK_EN	RESERVED	RESE	RVED	ADAPTIVE	D	RIVER_HEAD	ROOM[2:0]				
Name	Bit	Access	Description	scription							
SSCLK_EN	7	R/W	Enable spread spectrum function.								
RESERVED	6	R/W									
RESERVED	5:4	R/W									
ADAPTIVE	3	R/W	Enable adapt	tive boost contro	l.						
DRIVER_HEADROOM	2:0	R/W	contributes to 000 = HEADI 001 = HEADI 010 = HEADI 011 = HEADI 100 = HEADI 101 = HEADI 110 = HEADI	eadroom control. the MID compa ROOM_OFFSET ROOM_OFFSET ROOM_OFFSET ROOM_OFFSET ROOM_OFFSET ROOM_OFFSET ROOM_OFFSET ROOM_OFFSET	rator threshol + 875 mV + 750 mV + 625 mV + 500 mV + 375 mV + 250 mV + 125 mV		tor threshold and				

CFGE

Address AEh

CFGE register											
7	6	5	4	3	2	1	0				
STEP_UP[1:0]		STEP_	DN[1:0]	LED_FAUL	T_TH[2:0]	LED_CO	OMP_HYST[1:0]				
Name	Bit	Access	Description								
STEP_UP	7:6	R/W	Adaptive headroom UP step size 00 = 105 mV 01 = 210 mV 10 = 420 mV 11 = 840 mV								
STEP_DN	5:4	R/W	Adaptive headroom DOWN step size 00 = 105 mV 01 = 210 mV 10 = 420 mV 11 = 840 mV								
LED_FAULT_TH	3:2	R/W	LED headroom fault threshold. This sets the HIGH comparator threshold. 00 = 5V 01 = 4V 10 = 3V 11 = 2V								
LED_COMP_HYST	1:0	R/W	LED headrom comparison hysteresis. This sets the MID comparator threshold. 00 = DRIVER_HEADROOM + 1000 mV 01 = DRIVER_HEADROOM + 750 mV 10 = DRIVER_HEADROOM + 500 mV 11 = DRIVER_HEADROOM + 250 mV								

CFGF

Address AFh

CFGF register												
7	6	5	4 3 2 1 0									
REVISION												
Name	Bit	Access	Description									
REV	7:0	R/W	EPROM Settings Revision ID code									

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SNVS871E -JULY 2012-REVISED AUGUST 2013



REVISION HISTORY

Cł	nanges from Revision D (July 2013) to Revision E	Page
•	Added E13 column in EPROM tables; correct minor typo corrections to EPROM tables	45

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28-Aug-2013

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
LP8556SQ-E00/NOPB	ACTIVE	WQFN	RTW	24	1000	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM		L8556E0	Samples
LP8556SQ-E08/NOPB	ACTIVE	WQFN	RTW	24	1000	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM		L8556E8	Samples
LP8556SQ-E09/NOPB	ACTIVE	WQFN	RTW	24	1000	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM		L8556E9	Samples
LP8556SQE-E00/NOPB	ACTIVE	WQFN	RTW	24	250	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM		L8556E0	Samples
LP8556SQE-E08/NOPB	ACTIVE	WQFN	RTW	24	250	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM		L8556E8	Samples
LP8556SQE-E09/NOPB	ACTIVE	WQFN	RTW	24	250	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM		L8556E9	Samples
LP8556SQX-E00/NOPB	ACTIVE	WQFN	RTW	24	4500	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM		L8556E0	Samples
LP8556SQX-E08/NOPB	ACTIVE	WQFN	RTW	24	4500	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM		L8556E8	Samples
LP8556SQX-E09/NOPB	ACTIVE	WQFN	RTW	24	4500	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM		L8556E9	Samples
LP8556TME-E02/NOPB	ACTIVE	DSBGA	YFQ	20	250	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM		56E2	Samples
LP8556TME-E03/NOPB	ACTIVE	DSBGA	YFQ	20	250	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM		56E3	Samples
LP8556TME-E04/NOPB	ACTIVE	DSBGA	YFQ	20	250	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM		56E4	Samples
LP8556TME-E05/NOPB	ACTIVE	DSBGA	YFQ	20	250	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM		56E5	Samples
LP8556TME-E06/NOPB	ACTIVE	DSBGA	YFQ	20	250	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM		56E6	Samples
LP8556TME-E09/NOPB	ACTIVE	DSBGA	YFQ	20	250	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM		56E9	Samples
LP8556TME-E12/NOPB	PREVIEW	DSBGA	YFQ	20	250	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	-40 to 85	6E12	
LP8556TMX-E02/NOPB	ACTIVE	DSBGA	YFQ	20	3000	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM		56E2	Samples



PACKAGE OPTION ADDENDUM

28-Aug-2013

Orderable Device	Status	Package Type	_	Pins	_	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)		(3)		(4/5)	
LP8556TMX-E03/NOPB	ACTIVE	DSBGA	YFQ	20	3000	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM		56E3	Samples
LP8556TMX-E04/NOPB	ACTIVE	DSBGA	YFQ	20	3000	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM		56E4	Samples
LP8556TMX-E05/NOPB	ACTIVE	DSBGA	YFQ	20	3000	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM		56E5	Samples
LP8556TMX-E06/NOPB	ACTIVE	DSBGA	YFQ	20	3000	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM		56E6	Samples
LP8556TMX-E09/NOPB	ACTIVE	DSBGA	YFQ	20	3000	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM		56E9	Samples
LP8556TMX-E12/NOPB	PREVIEW	DSBGA	YFQ	20		Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	-40 to 85	6E12	

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free** (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.



PACKAGE OPTION ADDENDUM

28-Aug-2013

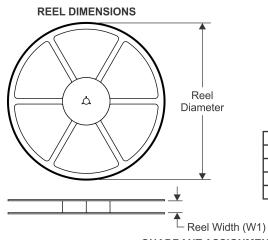
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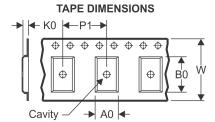
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PACKAGE MATERIALS INFORMATION

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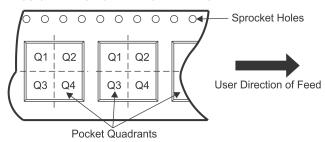
TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

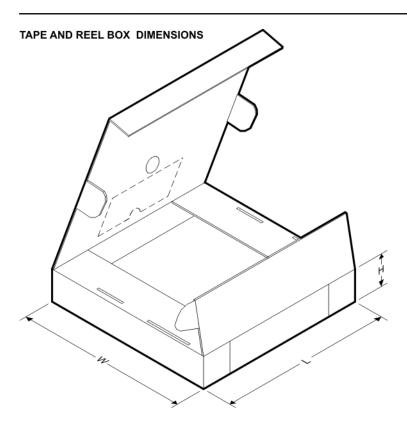
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

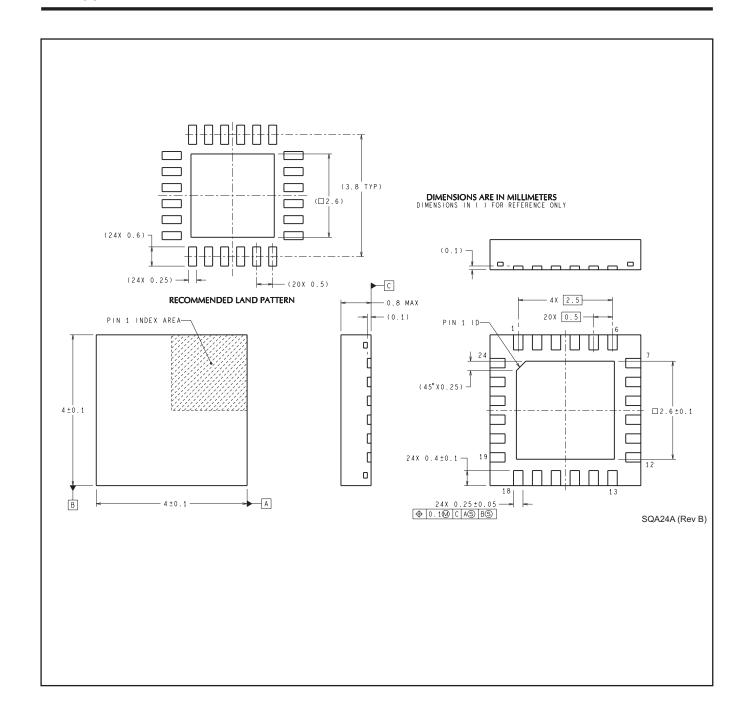
All dimensions are nominal													
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant	
LP8556TME-E02/NOPB	DSBGA	YFQ	20	250	178.0	8.4	1.83	2.49	0.76	4.0	8.0	Q1	
LP8556TME-E03/NOPB	DSBGA	YFQ	20	250	178.0	8.4	1.83	2.49	0.76	4.0	8.0	Q1	
LP8556TME-E04/NOPB	DSBGA	YFQ	20	250	178.0	8.4	1.83	2.49	0.76	4.0	8.0	Q1	
LP8556TME-E05/NOPB	DSBGA	YFQ	20	250	178.0	8.4	1.83	2.49	0.76	4.0	8.0	Q1	
LP8556TME-E06/NOPB	DSBGA	YFQ	20	250	178.0	8.4	1.83	2.49	0.76	4.0	8.0	Q1	
LP8556TME-E09/NOPB	DSBGA	YFQ	20	250	178.0	8.4	1.83	2.49	0.76	4.0	8.0	Q1	
LP8556TMX-E02/NOPB	DSBGA	YFQ	20	3000	178.0	8.4	1.83	2.49	0.76	4.0	8.0	Q1	
LP8556TMX-E03/NOPB	DSBGA	YFQ	20	3000	178.0	8.4	1.83	2.49	0.76	4.0	8.0	Q1	
LP8556TMX-E04/NOPB	DSBGA	YFQ	20	3000	178.0	8.4	1.83	2.49	0.76	4.0	8.0	Q1	
LP8556TMX-E05/NOPB	DSBGA	YFQ	20	3000	178.0	8.4	1.83	2.49	0.76	4.0	8.0	Q1	
LP8556TMX-E06/NOPB	DSBGA	YFQ	20	3000	178.0	8.4	1.83	2.49	0.76	4.0	8.0	Q1	
LP8556TMX-E09/NOPB	DSBGA	YFQ	20	3000	178.0	8.4	1.83	2.49	0.76	4.0	8.0	Q1	

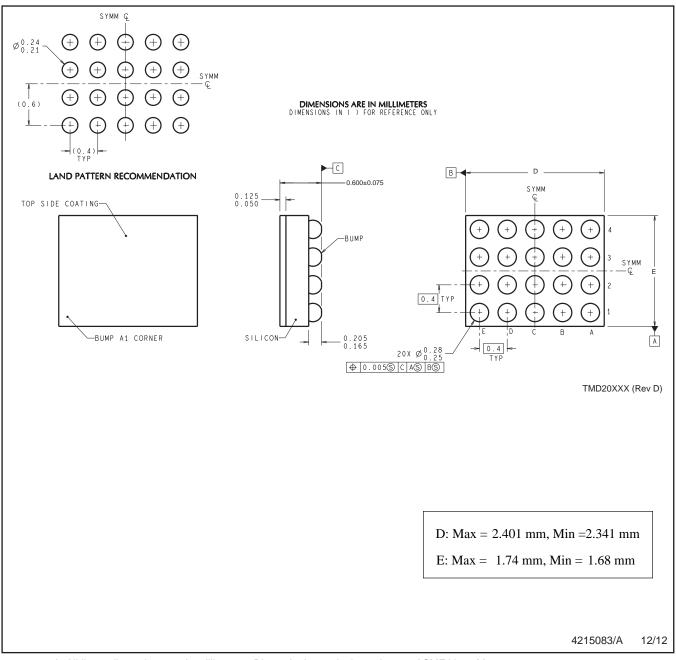
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*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
LP8556TME-E02/NOPB	DSBGA	YFQ	20	250	210.0	185.0	35.0
LP8556TME-E03/NOPB	DSBGA	YFQ	20	250	210.0	185.0	35.0
LP8556TME-E04/NOPB	DSBGA	YFQ	20	250	210.0	185.0	35.0
LP8556TME-E05/NOPB	DSBGA	YFQ	20	250	210.0	185.0	35.0
LP8556TME-E06/NOPB	DSBGA	YFQ	20	250	210.0	185.0	35.0
LP8556TME-E09/NOPB	DSBGA	YFQ	20	250	210.0	185.0	35.0
LP8556TMX-E02/NOPB	DSBGA	YFQ	20	3000	210.0	185.0	35.0
LP8556TMX-E03/NOPB	DSBGA	YFQ	20	3000	210.0	185.0	35.0
LP8556TMX-E04/NOPB	DSBGA	YFQ	20	3000	210.0	185.0	35.0
LP8556TMX-E05/NOPB	DSBGA	YFQ	20	3000	210.0	185.0	35.0
LP8556TMX-E06/NOPB	DSBGA	YFQ	20	3000	210.0	185.0	35.0
LP8556TMX-E09/NOPB	DSBGA	YFQ	20	3000	210.0	185.0	35.0





NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994. B. This drawing is subject to change without notice.

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